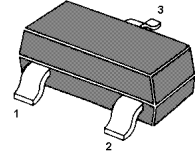


# MMBT3906

## PNP Silicon General Purpose Transistor

for switching and amplifier applications.

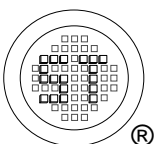
As complementary types the NPN transistors MMBT3904 is recommended.



1. Base 2. Emitter 3. Collector  
TO-236 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	200	mA
Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$



**SEMTECH ELECTRONICS LTD.**

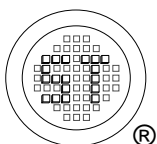


Dated : 16/03/2015 Rev: 01

# MMBT3906

## Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$ , $-I_C = 0.1\text{ mA}$	$h_{FE}$	60	-	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 1\text{ mA}$	$h_{FE}$	80	-	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 10\text{ mA}$	$h_{FE}$	100	300	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 50\text{ mA}$	$h_{FE}$	60	-	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 100\text{ mA}$	$h_{FE}$	30	-	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB} = 6\text{ V}$	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$ , $-I_B = 1\text{ mA}$	$-V_{CE(sat)}$	-	0.25	V
at $-I_C = 50\text{ mA}$ , $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.4	V
Base Emitter Saturation Voltage at $-I_C = 10\text{ mA}$ , $-I_B = 1\text{ mA}$	$-V_{BE(sat)}$	0.65	0.85	V
at $-I_C = 50\text{ mA}$ , $-I_B = 5\text{ mA}$	$-V_{BE(sat)}$	-	0.95	V
Current Gain Bandwidth Product at $-V_{CE} = 20\text{ V}$ , $-I_C = 10\text{ mA}$ , $f = 100\text{ MHz}$	$f_T$	250	-	MHz
Output Capacitance at $-V_{CB} = 5\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$	$C_{obo}$	-	4.5	pF
Delay Time at $-V_{CC} = 3\text{ V}$ , $-V_{BE} = 0.5\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = 1\text{ mA}$	$t_d$	-	35	ns
Rise Time at $-V_{CC} = 3\text{ V}$ , $-V_{BE} = 0.5\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = 1\text{ mA}$	$t_r$	-	35	ns
Storage Time at $-V_{CC} = 3\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = I_{B2} = 1\text{ mA}$	$t_s$	-	225	ns
Fall Time at $-V_{CC} = 3\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = I_{B2} = 1\text{ mA}$	$t_f$	-	75	ns

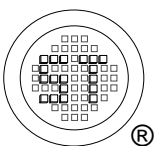
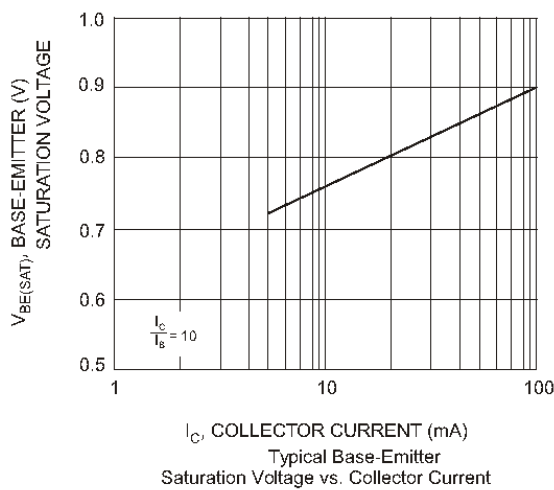
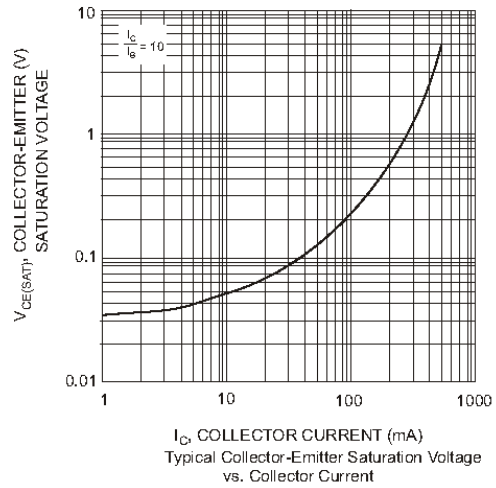
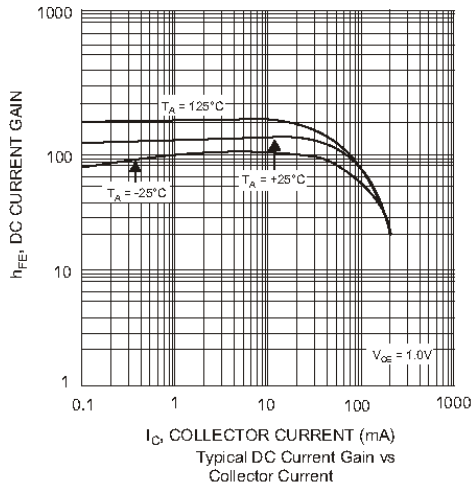
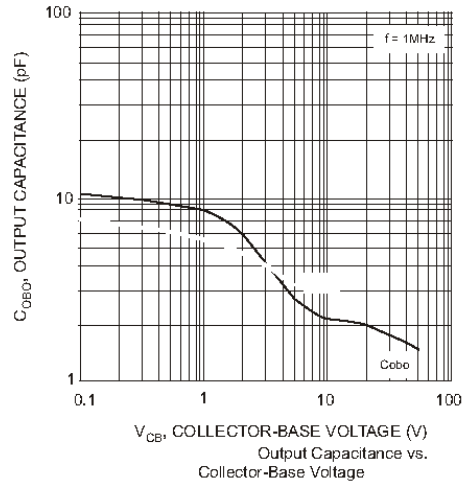
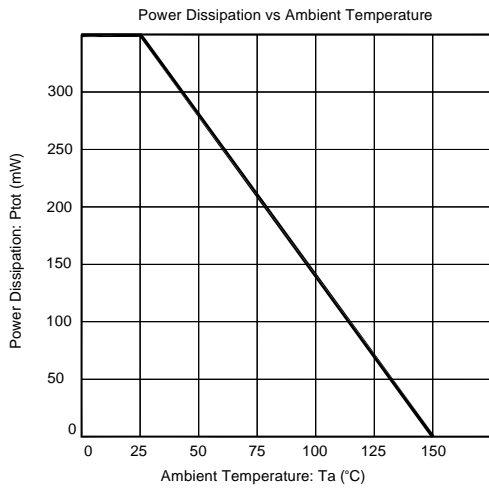


**SEMTECH ELECTRONICS LTD.**



Dated : 16/03/2015 Rev: 01

# MMBT3906



**SEMTECH ELECTRONICS LTD.**

